

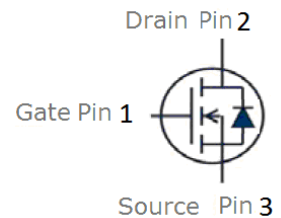
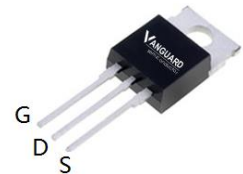
Features

- N-Channel, 10V Logic Level Control
- Enhancement mode
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=10\text{ V}$
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant



Part ID	Package Type	Marking	Tape and reel information
VS6880AT	TO-220AB	6880AT	50pcs/Tube

TO-220AB



Maximum ratings, at $T_A=25\text{ }^{\circ}\text{C}$, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		68	V
V_{GS}	Gate-Source voltage		± 25	V
I_S	Diode continuous forward current	$T_C=25^{\circ}\text{C}$	105	A
I_D	Continuous drain current @ $V_{GS}=10\text{ V}$	$T_C=25^{\circ}\text{C}$	105	A
		$T_C=100^{\circ}\text{C}$	75	A
I_{DM}	Pulse drain current tested ①	$T_C=25^{\circ}\text{C}$	420	A
I_{DSM}	Continuous drain current @ $V_{GS}=10\text{ V}$	$T_A=25^{\circ}\text{C}$	14	A
		$T_A=70^{\circ}\text{C}$	11	A
EAS	Avalanche energy, single pulsed ②		365	mJ
P_D	Maximum power dissipation	$T_C=25^{\circ}\text{C}$	115	W
P_{DSM}	Maximum power dissipation ③	$T_A=25^{\circ}\text{C}$	2	W
T_{STG}, T_J	Storage and Junction Temperature Range		-55 to 175	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.3	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^{\circ}\text{C/W}$

Typical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T _j = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	68	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =65V,V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _j =125°C)	V _{DS} =65V,V _{GS} =0V	--	--	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±25V,V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =250μA	2.5	2.9	3.9	V
R _{DS(ON)}	Drain-Source On-State Resistance ④	V _{GS} =10V, I _D =40A	--	6.1	8	mΩ
Dynamic Electrical Characteristics @ T _j = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =30V,V _{GS} =0V, f=1MHz	4500	5855	7000	pF
C _{oss}	Output Capacitance		150	250	350	pF
C _{rss}	Reverse Transfer Capacitance		100	175	250	pF
R _g	Gate Resistance	f=1MHz	--	3	--	Ω
Q _g	Total Gate Charge	V _{DS} =35V,I _D =40A, V _{GS} =10V	--	86	--	nC
Q _{gs}	Gate-Source Charge		--	14	--	nC
Q _{gd}	Gate-Drain Charge		--	23	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =35V, I _D =40A, R _G =3Ω, V _{GS} =10V	--	15	--	nS
t _r	Turn-on Rise Time		--	11.8	--	nS
t _{d(off)}	Turn-Off Delay Time		--	51	--	nS
t _f	Turn-Off Fall Time		--	18	--	nS
Source- Drain Diode Characteristics@ T _j = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =40A,V _{GS} =0V	--	0.9	1.2	V
t _{rr}	Reverse Recovery Time	T _j =25°C ,I _{sd} =40A, V _{GS} =0V di/dt=100A/μs	--	44	--	nS
Q _{rr}	Reverse Recovery Charge				33	

NOTE:

- ① Repetitive rating; pulse width limited by max junction temperature.
- ② Limited by T_{Jmax} , starting $T_j = 25^\circ\text{C}$, $L = 0.5\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 30A$, $V_{GS} = 10V$. Part not recommended for use above this value
- ③ The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C .
- ④ Pulse width $\leq 300\mu s$; duty cycles $\leq 2\%$.

%.

Typical Characteristics

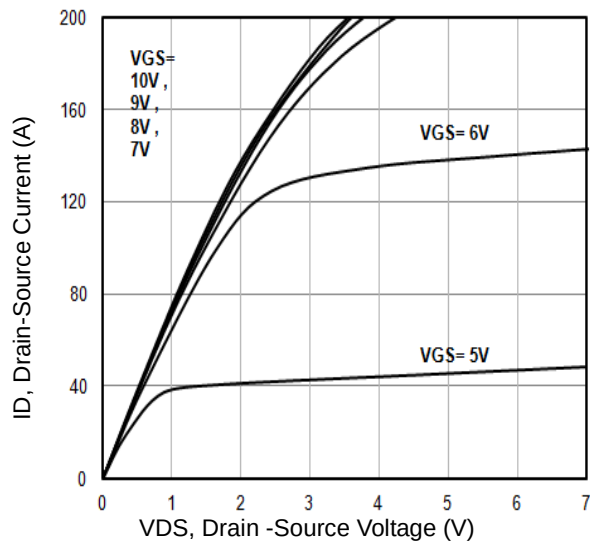


Fig1. Typical Output Characteristics

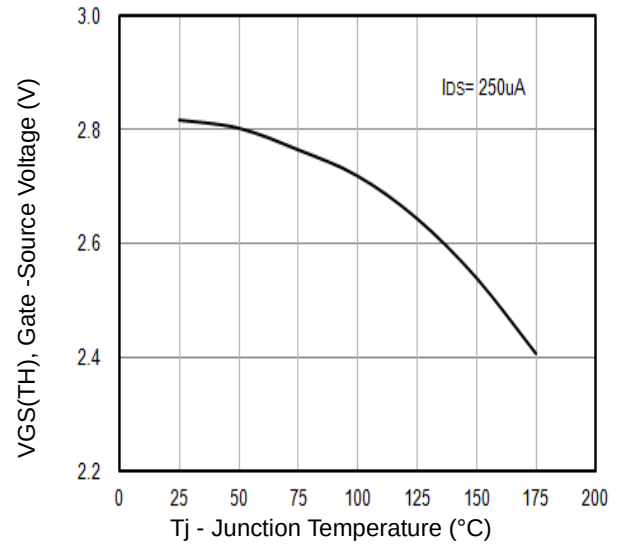


Fig2. $V_{GS(TH)}$ Gate-Source Voltage Vs. T_J

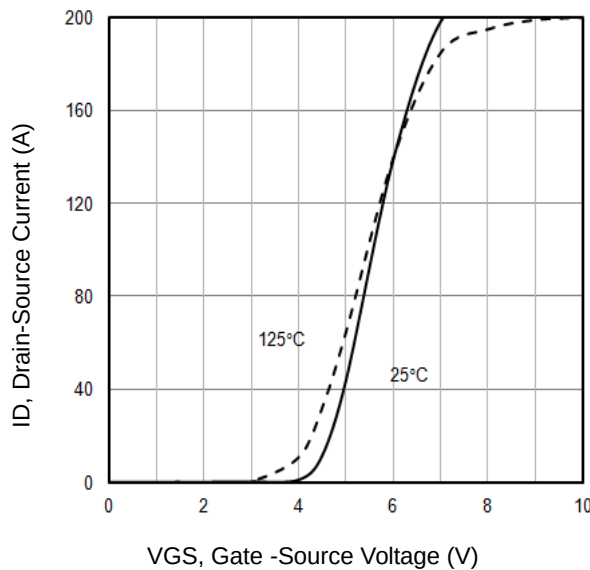


Fig3. Typical Transfer Characteristics

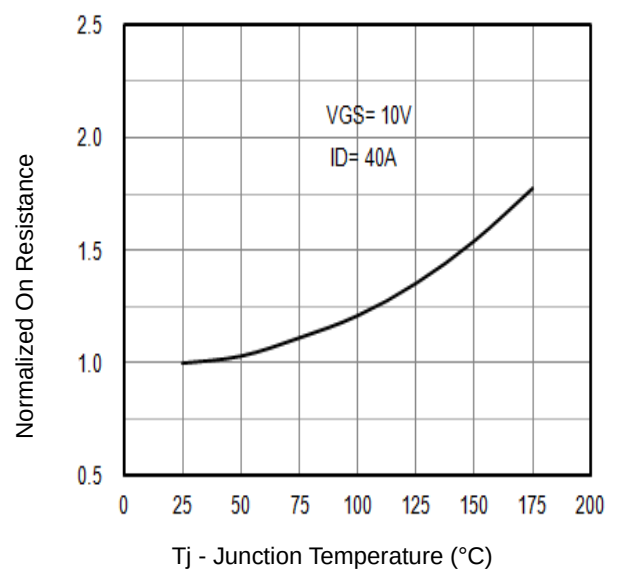


Fig4. Normalized On-Resistance Vs. Temperature

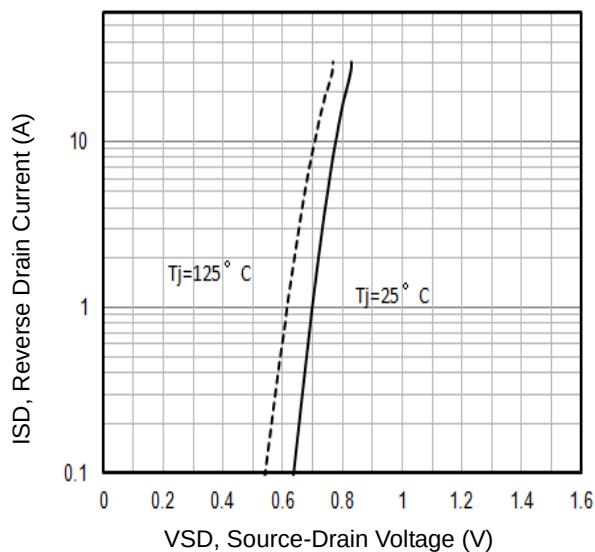


Fig5. Typical Source-Drain Diode Forward Voltage

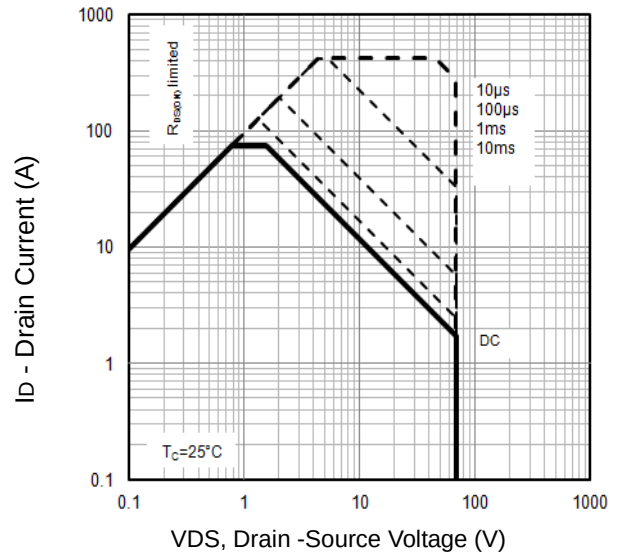


Fig6. Maximum Safe Operating Area

Typical Characteristics

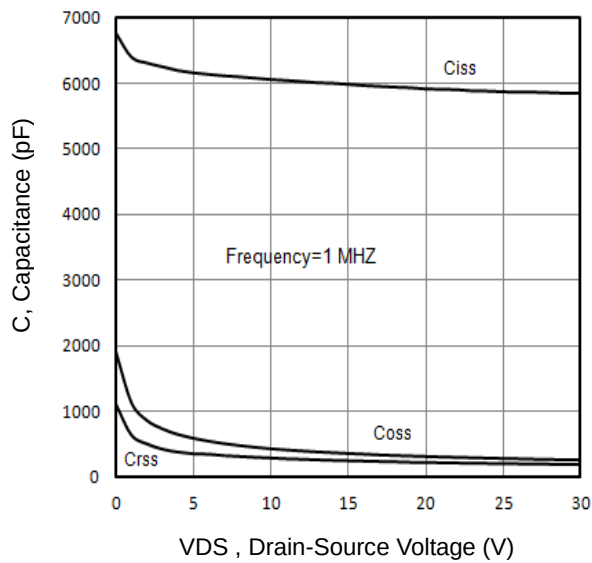


Fig7. Typical Capacitance Vs. Drain-Source Voltage

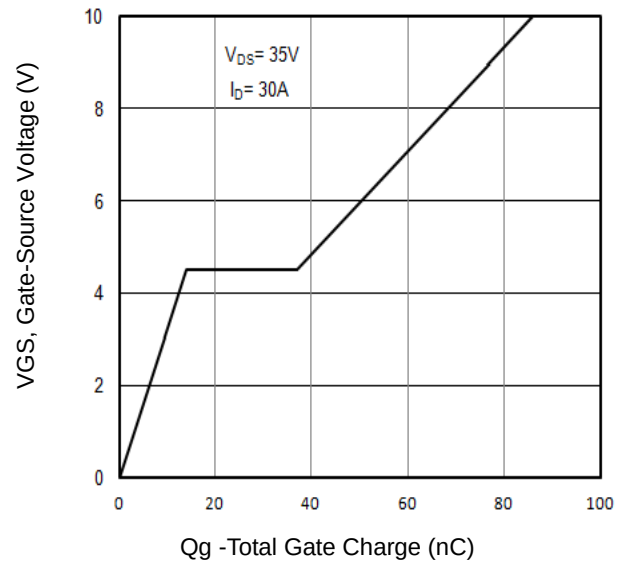


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

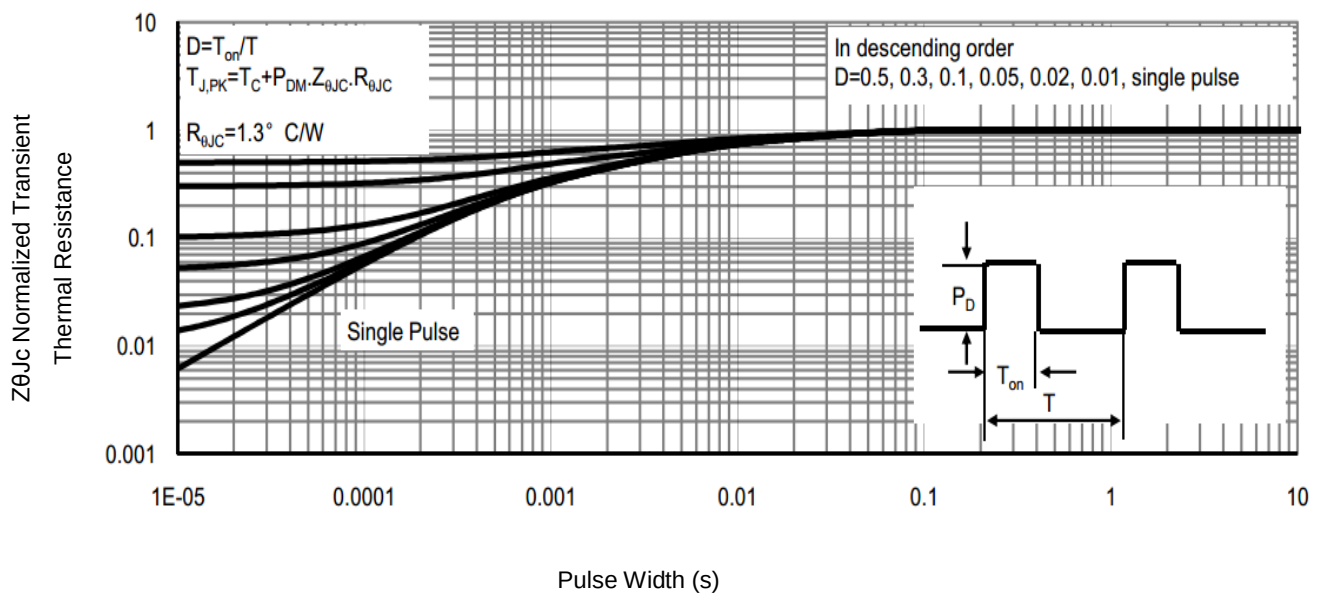


Fig9 . Normalized Maximum Transient Thermal Impedance

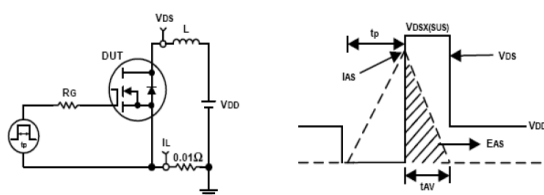


Fig10. Unclamped Inductive Test Circuit and waveforms

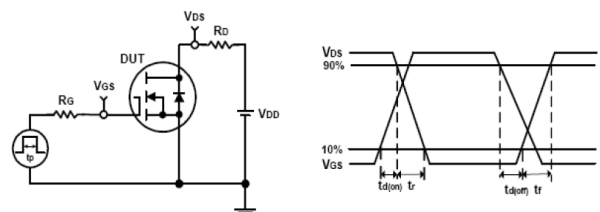
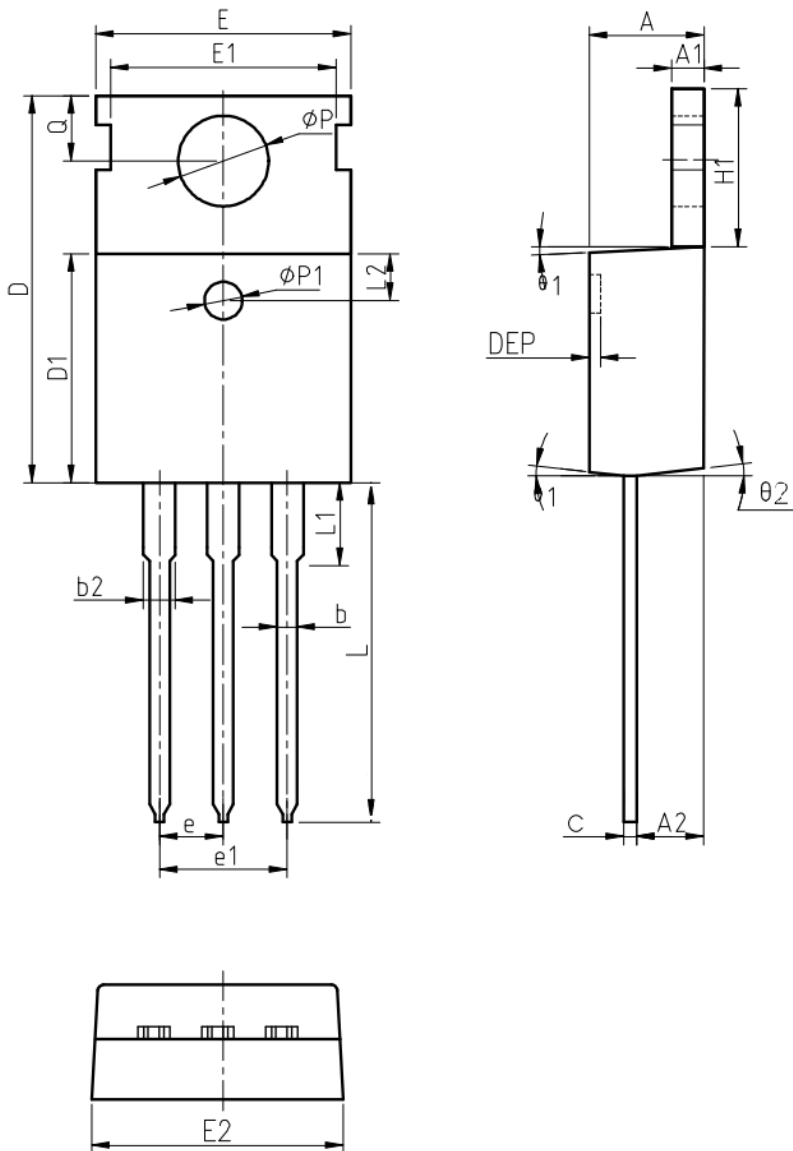


Fig11. Switching Time Test Circuit and waveforms

TO-220AB Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	4.30	4.52	4.70
A1	1.15	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	1.00
b2	1.17	1.32	1.50
c	0.45	0.50	0.61
D	15.30	15.65	15.90
D1	9.00	9.20	9.40
DEP	0.05	0.10	0.25
E	9.66	9.90	10.28
E1	-	8.70	-
E2	9.80	10.00	10.20
$\phi P1$	1.40	1.50	1.60
e	2.54 BSC		
e1	5.08 BSC		
H1	6.40	6.50	6.80
L	12.70	-	14.27
L1	-	-	3.95
L2	2.40	2.50	2.60
ϕP	3.53	3.60	3.70
Q	2.70	2.80	2.90
$\theta 1$	5 °	7 °	9 °
$\theta 2$	1 °	3 °	5 °

Notes:

1. Refer to JEDEC TO-220 variation AB
2. Dimension "D" and "E" do NOT include mold flash. Mold flash shall not exceed 0.127mm per side.

Customer Service

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